

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Claims 1-22 (canceled).

Claim 23 (new): A method for fabricating a semiconductor device, the method including:

forming an amorphous silicon film on a substrate;

preprocessing the amorphous silicon film by modifying the amorphous silicon film to prepare the amorphous silicon film to be made polycrystalline;

laser processing the amorphous silicon film modified through the preprocessing step for producing a polycrystalline silicon film; and

laser power inspecting/extracting for determining a laser power based on a predetermined inspection performed on a predetermined region of the amorphous silicon film having undergone the preprocessing step; wherein

the laser processing step uses the laser power determined in the laser power inspection/extraction step.

Claim 24 (new): The method of claim 23, wherein the laser power inspection/extraction step includes determining the laser power through inspection using spectroscopy.

Claim 25 (new): The method of claim 24, wherein the spectroscopy is performed at a measurement wavelength of about 700 nm to about 800 nm.

Claim 26 (new): The method of claim 23, wherein the laser power inspection/extraction step includes determining the laser power through inspection using

imaging whereby light shines on a measurement spot to detect an image acquired by targeting the measurement spot.

Claim 27 (new): The method of claim 26, wherein the inspection using the imaging includes inspecting for the presence of a foreign object or an abnormality in film quality.

Claim 28 (new): The method of claim 24, wherein the inspection using the spectroscopy is performed with measurement light shining on a measurement spot from around the measurement spot.

Claim 29 (new): The method of claim 23, wherein the laser power inspection/extraction step includes performing an inspection adjacent laser processing equipment that performs the laser processing in the laser processing step.

Claim 30 (new): The method of claim 23, wherein the laser power inspection/extraction step includes inspecting a film surface on the substrate.

Claim 31 (new): The method of claim 23, wherein the laser power inspection/extraction step includes performing an inspection by using equipment provided with both an inspection function for inspecting the polycrystalline silicon film and an inspection function for determining the laser power.

Claim 32 (new): The method of claim 23, wherein the laser power inspection/extraction step includes setting a measurement fixed-quantity value against which to evaluate measurement results.

Claim 33 (new): The method of claim 32, wherein the measurement fixed-quantity value is determined by using equipment having a calibration substrate placed thereon and provided with a function for performing calibration.

Claim 34 (new): The method of claim 23, wherein the laser power inspection/extraction step includes performing an inspection by using equipment provided with both a function for inspecting the polycrystalline silicon film and a function for automatically determining an optimum laser power value and automatically feeding the automatically determined optimum laser power value to laser processing equipment used in the laser processing step.

Claim 35 (new): The method of claim 23, wherein the laser processing step includes using a laser power about 5 mJ or about 10 mJ lower than an optimum laser power value determined in the laser power inspection/extraction step.

Claim 36 (new): The method of claim 23, wherein the laser power inspection/extraction step includes performing multiple-point measurement inspection on the polycrystalline silicon film.

Claim 37 (new): The method of claim 23, wherein the laser power inspection/extraction step includes inspecting, before the laser processing, the film on the substrate to find a ratio of amorphous silicon film to polycrystalline silicon film.

Claim 38 (new): The method of claim 23, wherein the laser power inspection/extraction step includes inspecting, after the laser processing, the film on the substrate to find a ratio of amorphous silicon film to polycrystalline silicon film.

Claim 39 (new): The method of claim 23, wherein the laser power inspection/extraction step includes inspecting, both before and after the laser processing, the film on the substrate to find a ratio of amorphous silicon film to polycrystalline silicon film.

Claim 40 (new): An apparatus for inspecting a semiconductor, the apparatus comprising:

- a light-emitting portion arranged to emit light;
- an illuminating member arranged to reflect the light and to direct the light to a predetermined substrate;
- a magnifying portion arranged to receive the light reflected from the predetermined substrate and magnify the light;
- a camera portion arranged to convert the light magnified by the magnifying portion into image data;
- a processing portion arranged to read the image data from the camera portion and perform predetermined data processing on the image data;
- a memory portion arranged to store an evaluation condition against which a result of the predetermined data processing is evaluated to determine a predetermined value;
- an evaluating portion arranged to evaluate the result of the predetermined data processing against the evaluation condition to determine the predetermined value; and
- a transmitting portion arranged to establish a connection for communication with an external apparatus and transmit the predetermined value to the external apparatus.

Claim 41 (new): The apparatus of claim 40, wherein the illuminating member is arranged to direct the light to the predetermined substrate so that the light strikes the predetermined substrate at an angle of about 30 degrees to about 60 degrees.

Claim 42 (new): The apparatus of claim 40, further comprising:

- a spectroscopic apparatus arranged to shine light of a plurality of different wavelengths in a visible spectrum region to the predetermined substrate, then receive the light reflected from the predetermined substrate to acquire spectroscopic data, and then feed the spectroscopic data to the processing portion; wherein
 - the processing portion is arranged to convert the spectroscopic data into light intensity distribution data of the reflected light at the different wavelengths.

Claim 43 (new): The apparatus of claim 42, wherein the different wavelengths are from about 700 nm to about 800 nm when amorphous silicon film or polycrystalline silicon film is formed on the substrate.

Claim 44 (new): The apparatus of claim 40, wherein the evaluating portion is arranged to determine an optimum laser power value at which to modify the amorphous silicon film into polycrystalline silicon film when the amorphous silicon film or polycrystalline silicon film is formed on the substrate.